

## Silicon NPN Power Transistors

2SC3156

## DESCRIPTION

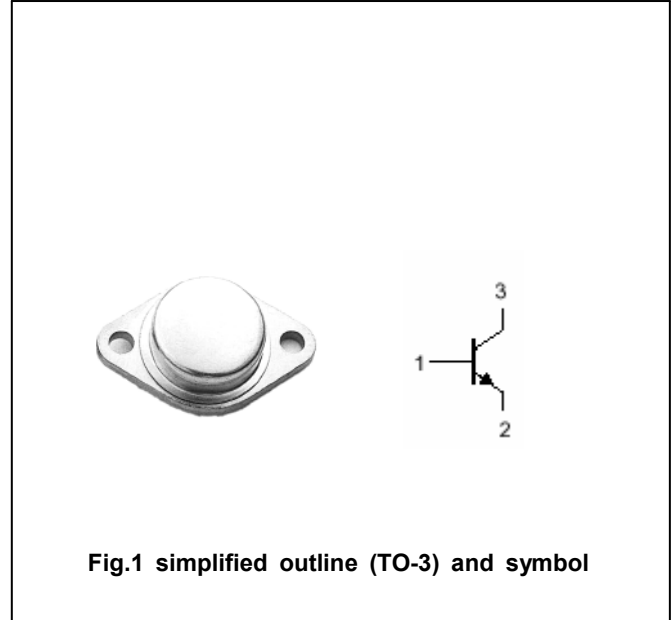
- With TO-3 package
- High breakdown voltage  
:  $V_{CBO}=900V(\text{Min})$
- Fast switching speed.
- Wide area of safe operation

## APPLICATIONS

- For switching regulator applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS( $T_C=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	900	V
$V_{CEO}$	Collector-emitter voltage	Open base	800	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		6	A
$I_{CP}$	Collector current-peak	$PW \leq 300\mu\text{s}$ , Duty Cycle $\leq 10\%$	20	A
$I_B$	Base current		3	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	120	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

## Silicon NPN Power Transistors

## 2SC3156

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA ; R <sub>BE</sub> =∞	800			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	900			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			2.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.4A ; V <sub>CE</sub> =5V	10			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =5V	8			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V, f=1MHz		120		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V		15		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =4A; I <sub>B1</sub> =0.8A; I <sub>B2</sub> =-1.6A V <sub>CC</sub> =400V ,R <sub>L</sub> =100Ω			1.0	μs
t <sub>s</sub>	Storage time				2.5	μs
t <sub>f</sub>	Fall time				0.7	μs

Silicon NPN Power Transistors

2SC3156

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)